



NCV8401A, NCV8401B

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Clamped Breakdown Voltage ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\text{ }\mu\text{Adc}$) ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\text{ }\mu\text{Adc}$, $T_J = 150\text{ C}$) (Note 4)	$V_{(BR)DSS}$	42 42	46 44	50 50	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 32\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 32\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 150\text{ C}$) (Note 4)	I_{DSS}		1.5 6.5	5.0	μAdc
Gate Input Current ($V_{GS} = 5.0\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSSF}		50	100	μAdc

ON CHARACTERISTICS

Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.2\text{ mAdc}$) Threshold Temperature Coefficient	$V_{GS(th)}$	1.0	1.8 5.0	2.0	Vdc -mV/ C
Static Drain-to-Source On-Resistance (Note 5) ($V_{GS} = 10\text{ Vdc}$, $I_D = 5.0\text{ Adc}$, $T_J @ 25\text{ C}$) ($V_{GS} = 10\text{ Vdc}$, $I_D = 5.0\text{ Adc}$, $T_J @ 150\text{ C}$) (Note 4)	$R_{DS(on)}$		23 43	29 55	$\text{m}\Omega$
Static Drain-to-Source On-Resistance (Note 5) ($V_{GS} = 5.0\text{ Vdc}$, $I_D = 5.0\text{ Adc}$, $T_J @ 25\text{ C}$) ($V_{GS} = 5.0\text{ Vdc}$, $I_D = 5.0\text{ Adc}$, $T_J @ 150\text{ C}$) (Note 4)	$R_{DS(on)}$		28 50	34 60	$\text{m}\Omega$
Source-Drain Forward On Voltage ($I_S = 5\text{ A}$, $V_{GS} = 0\text{ V}$)	V_{SD}		0.80	1.1	V

SWITCHING CHARACTERISTICS (Note 4)

Turn-ON Time (10% V_{IN} to 90% I_D)	$V_{IN} = 0\text{ V to } 5\text{ V}$, $V_{DD} = 25\text{ V}$ $I_D = 1.0\text{ A}$, Ext R
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TYPICAL PERFORMANCE CURVES

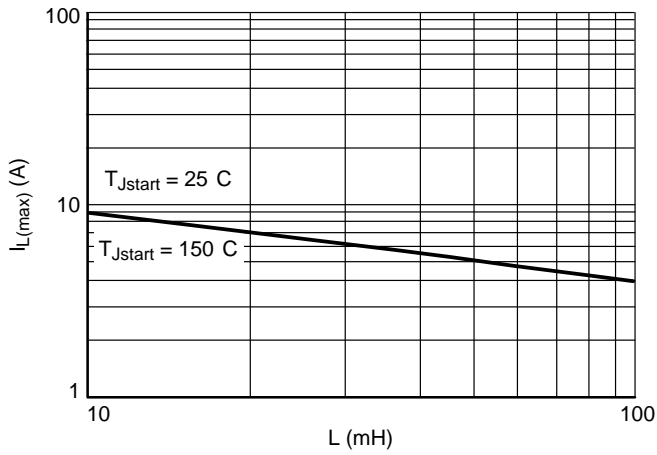


Figure 2. Single Pulse Maximum Switch off Current vs. Load Inductance

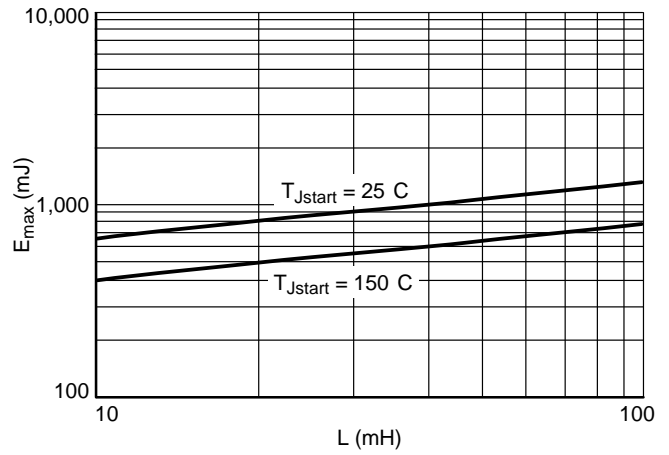
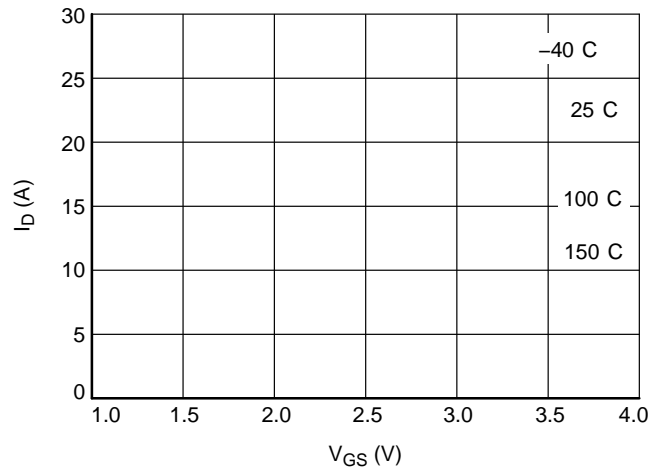
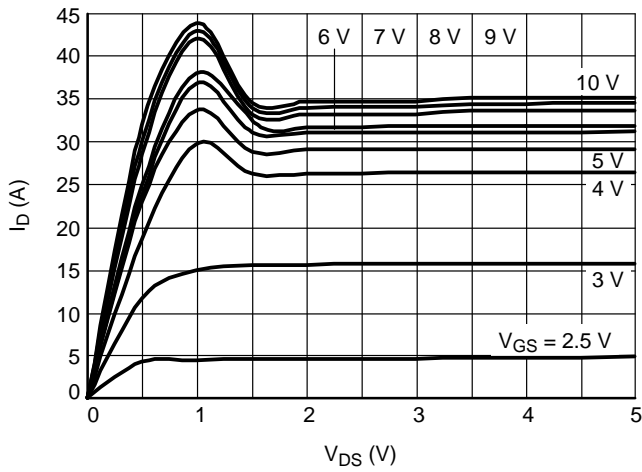


Figure 3. Single Pulse Maximum Switching Energy vs. Load Inductance



TYPICAL PERFORMANCE CURVES

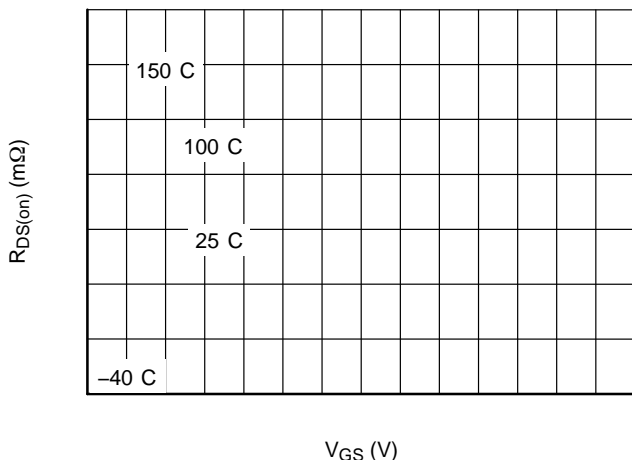


Figure 8. $R_{DS(on)}$ vs. Gate Source Voltage

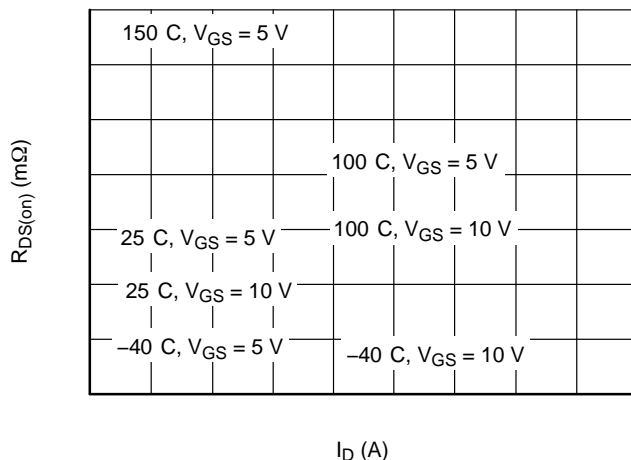


Figure 9. $R_{DS(on)}$ vs. Drain Current

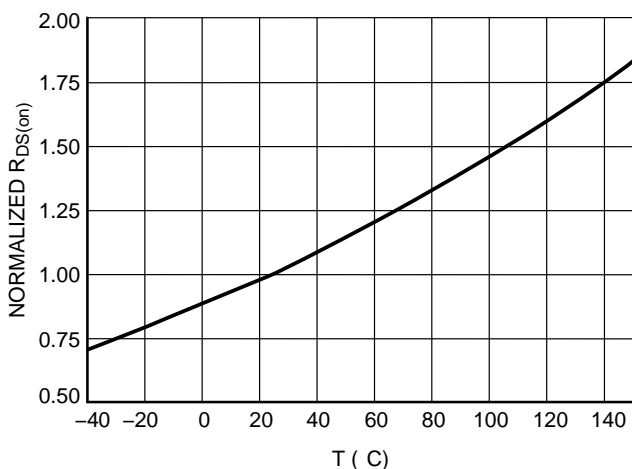


Figure 10. Normalized $R_{DS(on)}$ vs. Temperature ($I_D = 5$ A)

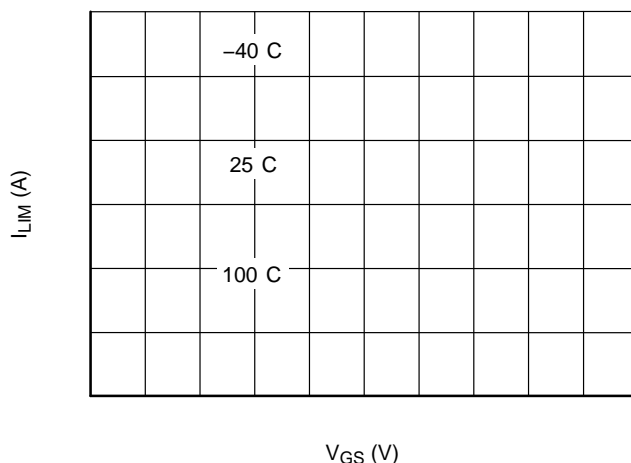


Figure 11. Current Limit vs. Gate Source Voltage ($V_{DS} = 10$ V)

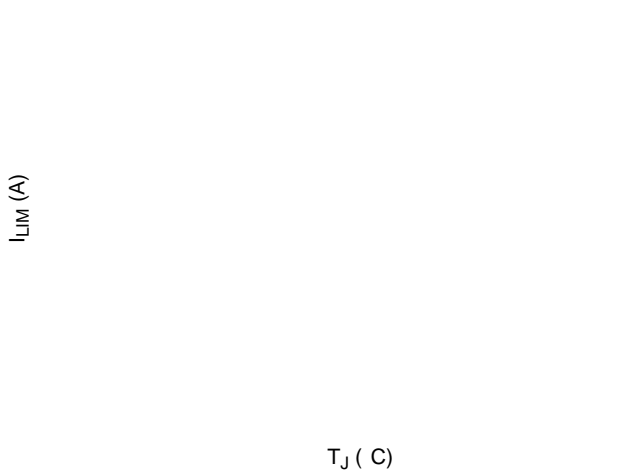


Figure 12. Current Limit vs. Junction Temperature ($V_{DS} = 10$ V)

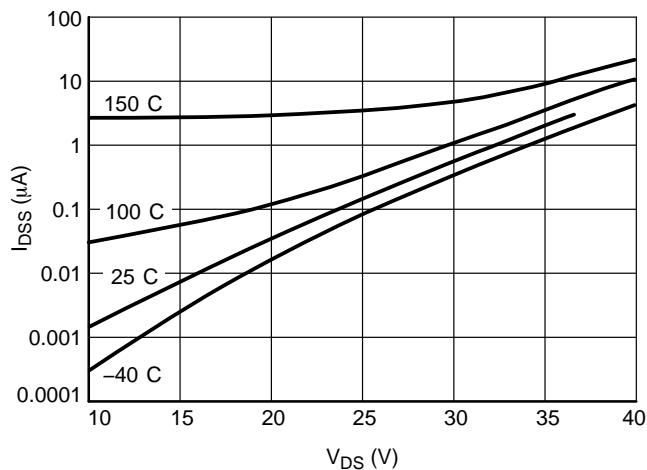


Figure 13. Drain to Source Leakage Current ($V_{GS} = 0$ V)

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TEST CIRCUITS AND WAVEFORMS

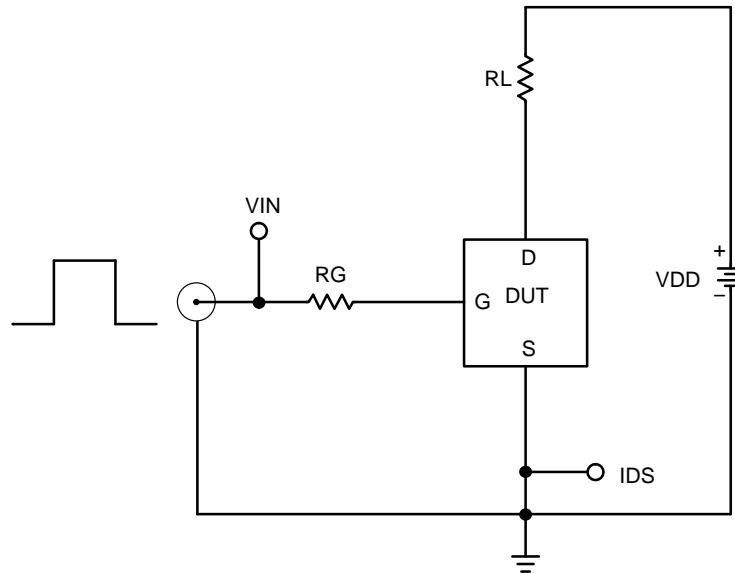


Figure 22. Resistive Load Switching Test Circuit

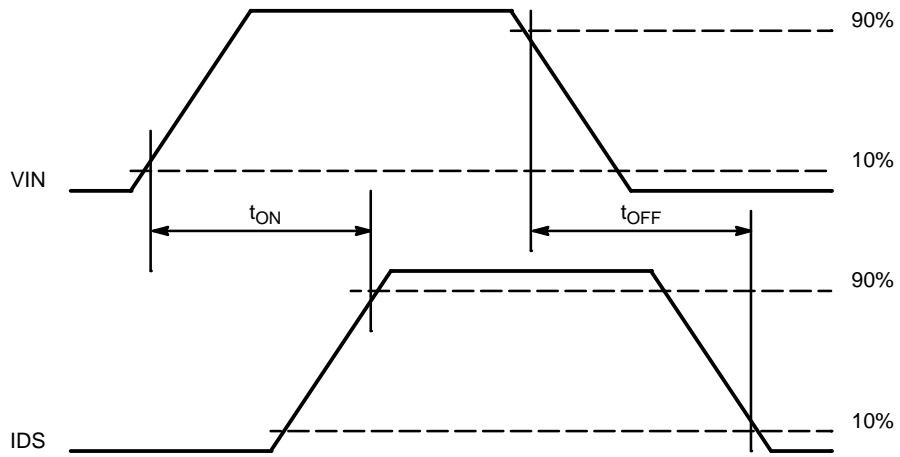
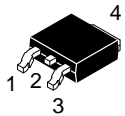


Figure 23. Resistive Load Switching Waveforms



SCALE 1:1

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE	STYLE 4: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 8: PIN 1. N/C 2. CATHODE 3. ANODE 4. CATHODE	STYLE 9: PIN 1. ANODE 2. CATHODE 3. RESISTOR ADJUST 4. CATHODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

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